



**Advanced Power
Electronics Corp.**

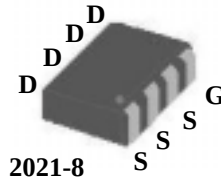
AP1801GU

Pb Free Plating Product

P-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ Capable of 2.5V gate drive
- ▼ Lower on-resistance
- ▼ Surface mount package

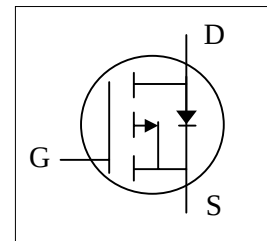


BV_{DSS}	-20V
$R_{DS(ON)}$	70m Ω
I_D	-4A

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The 2021-8 J-lead package provides good on-resistance performance and space saving like SC-70-6.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current ³	-4	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current ³	-3.3	A
I_{DM}	Pulsed Drain Current ^{1,2}	20	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	1.6	W
	Linear Derating Factor	0.013	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient ³ Max.	78	$^\circ\text{C}/\text{W}$

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =-1mA	-	0.01	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-4.8A	-	-	52	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	-	70	mΩ
		V _{GS} =-2.5V, I _D =-2A	-	-	100	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-0.5	-	-1.2	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-4A	-	10	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =-20V, V _{GS} =0V	-	-	-1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =-16V, V _{GS} =0V	-	-	-10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±12V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =-4A	-	11	18	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-16V	-	2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	4	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-10V	-	10	-	ns
t _r	Rise Time	I _D =-1A	-	16	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =-5V	-	26	-	ns
t _f	Fall Time	R _D =10Ω	-	16	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	740	1180	pF
C _{oss}	Output Capacitance	V _{DS} =-20V	-	160	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	130	-	pF
R _g	Gate Resistance	f=1.0MHz	-	6.6	10	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Forward On Voltage ²	I _S =-1.3A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =4A, V _{GS} =0V,	-	29	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	20	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mounted on 1 in² copper pad of FR4 board , t ≤5sec ; 125 °C/W at steady state.

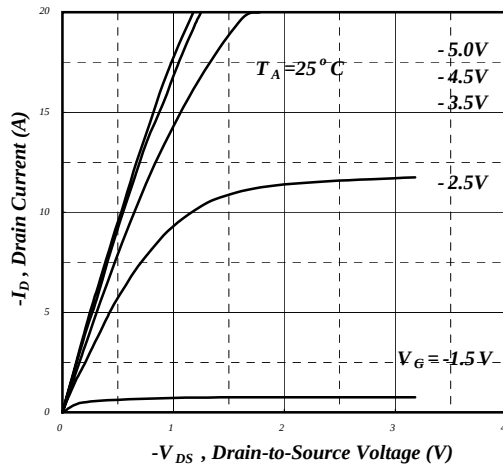


Fig 1. Typical Output Characteristics

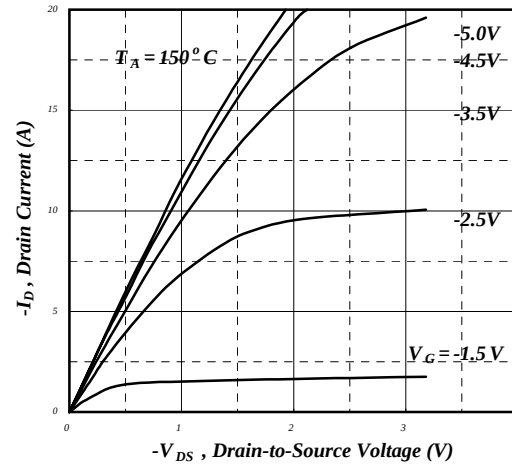


Fig 2. Typical Output Characteristics

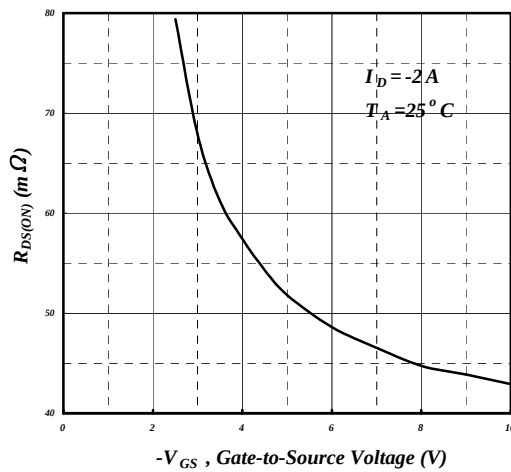


Fig 3. On-Resistance v.s. Gate Voltage

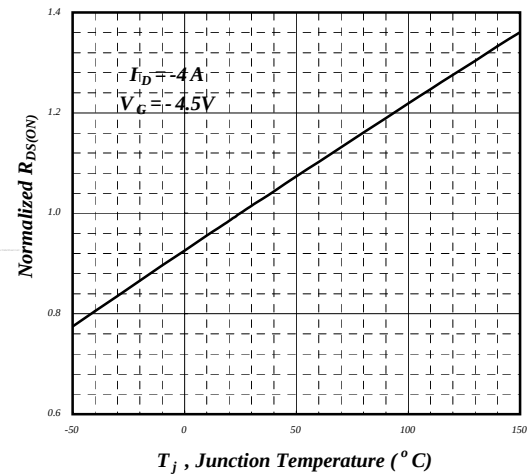


Fig 4. Normalized On-Resistance v.s. Junction Temperature

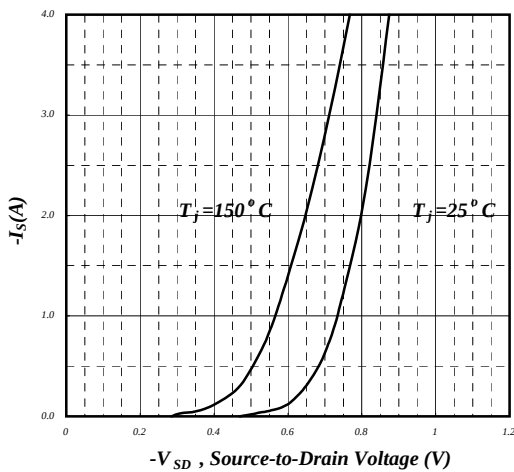


Fig 5. Forward Characteristic of Reverse Diode

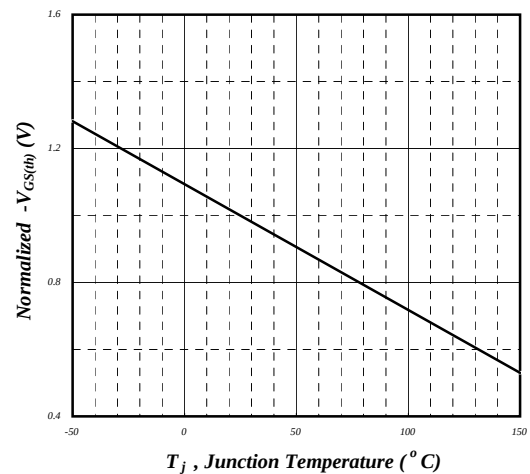


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

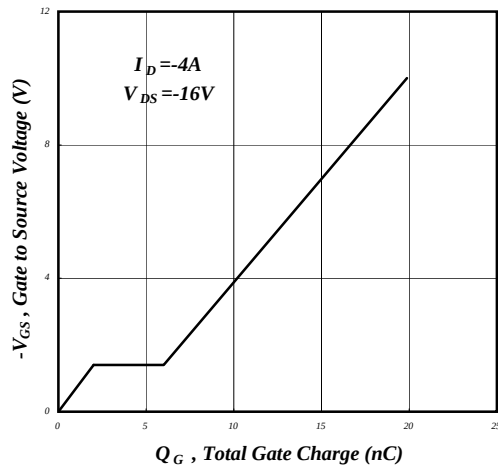


Fig 7. Gate Charge Characteristics

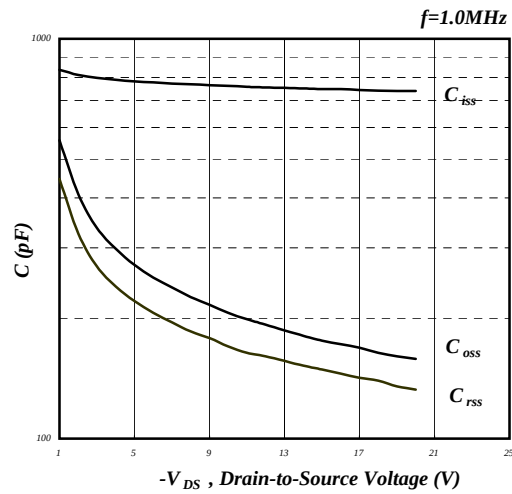


Fig 8. Typical Capacitance Characteristics

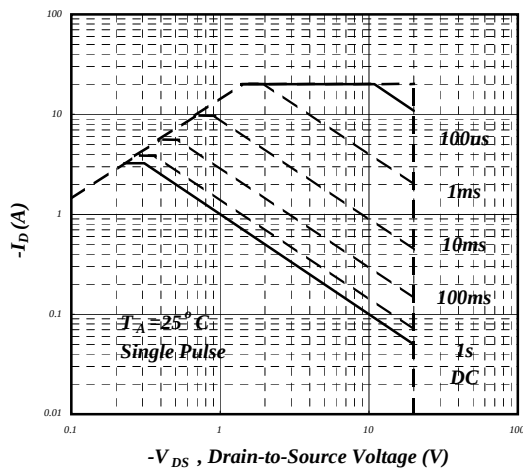


Fig 9. Maximum Safe Operating Area

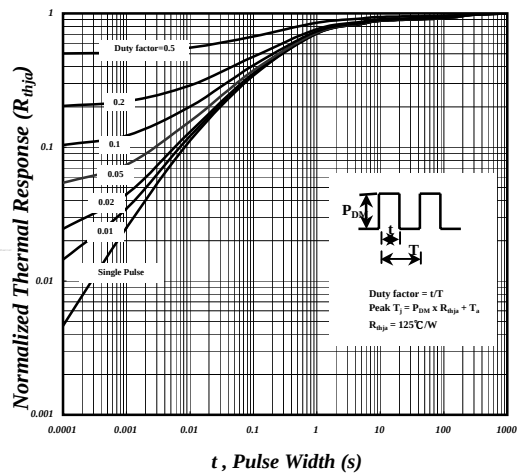


Fig 10. Effective Transient Thermal Impedance

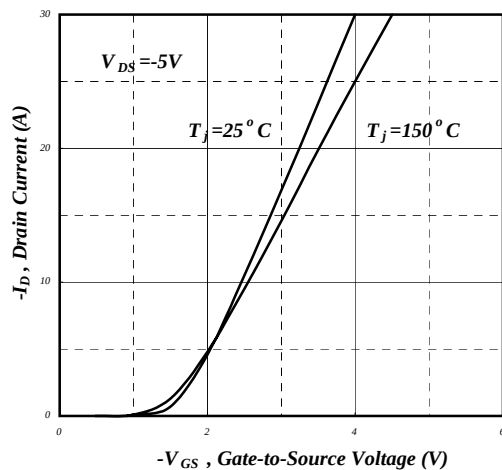


Fig 11. Transfer Characteristics

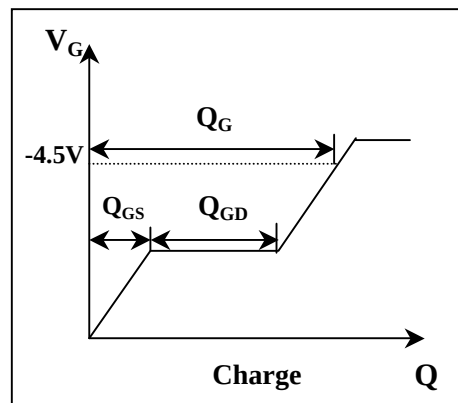


Fig 12. Gate Charge Waveform